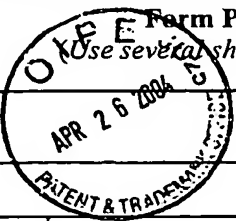
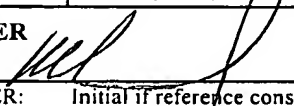


<b>LIST OF REFERENCES CITED BY APPLICANT</b> <div style="text-align: center;">  </div>				ATTY. DOCKET NO.: <b>4717-11500</b>		APPLICATION NO.: <b>10/716,451</b>		
APPLICANT: <b>Fabrice LETERTRE</b>				FILING DATE: <b>November 20, 2003</b>		GROUP: <b>1765</b>		
<b>U.S. PATENT DOCUMENTS</b>								
*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
[Signature]	A1	6,328,796 B1	12/2001	Kub et al.	117	94		
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<b>FOREIGN PATENT DOCUMENTS</b>								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
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[Signature]	B5	EP 1 245 702	02/2002	EPO				
[Signature]	B6	JP 2003 183097	07/2003	Japan (with English abstract)			X	
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[Signature]	C1	Hugonnard-Bruyère, E., et al., "Deep Level Defectss in H <sup>+</sup> Implanted 6H-SiC Epilayers and in Silicon Carbide on Insulator Structures", <i>Materials Science and Engineering B</i> , Vol. 61-62, pp. 382-388 (1999)						
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[Signature]	C3	Müller, S.G, et al., "Progress in the Industrial Production of SiC Substrates for Semiconductor Devices", <i>Materials and Science Engineering B</i> , Vol. 80, No. 1-3, pp. 327-331 (2001)						
[Signature]	C4	Tsvetkov, V. et al., "SiC Seeded Boule Growth", <i>Materials Science Forum</i> , Vols. 264-268, pp. 3-8 (1998)						
[Signature]	C5	Tsuetkov, V.F. et al., "Recent Progress in SiC Crystal Growth", <i>Inst. Phys. Conf. Ser.</i> , No. 142, Chap. 1, pp. 17-22 (1996)						
EXAMINER 				DATE CONSIDERED <b>12/23/05</b>				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								